

**100 V, 6 A PNP high power bipolar transistor** 21 January 2015

Product data sheet

### 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61006NY

### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

### 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1.   Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-100	V
I <sub>C</sub>	collector current			-	-	-6	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}; \text{ single pulse}$		-	-	-12	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -6 A; $I_B$ = -600 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed		-	85	270	mΩ

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# 5. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	E	emitter	mb	С	
2	E	emitter		в	
3	3 E emitter	q	۲۳. ۲۳.		
4	В	base	មូមូមូម	sym132	
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)		

# 6. Ordering information

Table 3.       Ordering information						
Type number	Package					
	Name	Description	Version			
PHPT61006PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT61006PY	1006PAB

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-6	А
I <sub>CM</sub>	peak collector current	$t_p \le 1$ ms; single pulse		-	-12	А
I <sub>B</sub>	base current			-	-1	А
I <sub>BM</sub>	peak base current	$t_p \le 1 ms$ ; pulsed		-	-2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			<u>[3]</u>	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

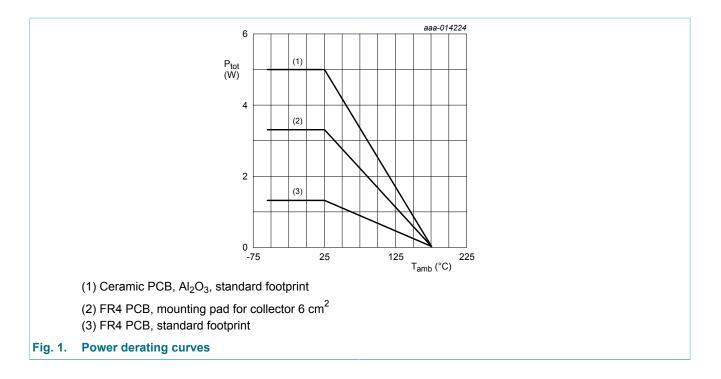
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[4] Power dissipation from junction to mounting base.

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### 9. Thermal characteristics

#### Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub> thermal resista from junction t ambient	thermal resistance		[1]	-	-	115	K/W
	-		[2]	-	-	45	K/W
			<u>[3]</u>	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

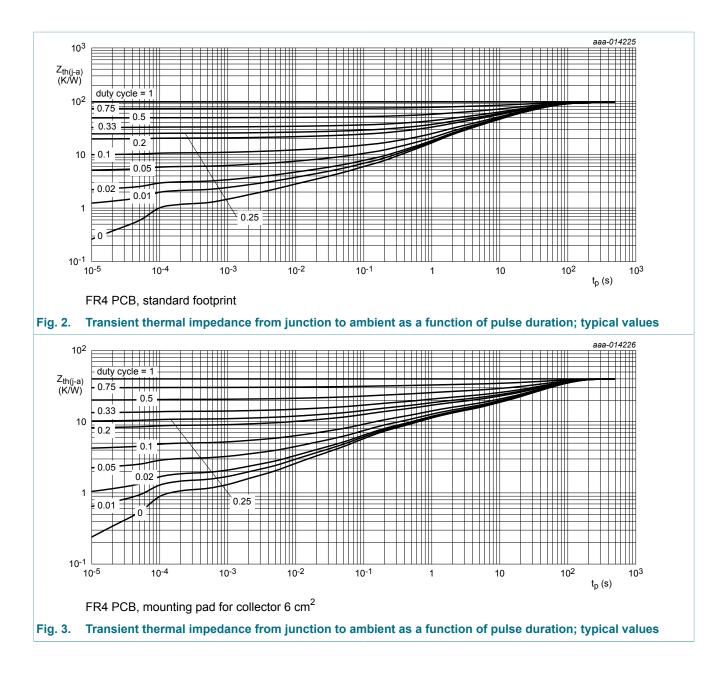
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

footprint.
 [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



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### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -80 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	170	305	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	160	275	-	
		$V_{CE} = -2 \text{ V; } I_C = -3 \text{ A; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02; \text{ T}_{amb} = 25 ^\circ\text{C; } \text{pulsed}$	45	90	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -6 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	10	20	-	
02041	collector-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -50 mA; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-75	-130	mV
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-150	-240	mV
		$I_{C}$ = -6 A; $I_{B}$ = -600 mA; pulsed; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-900	-1600	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -6 A; $I_{B}$ = -600 mA; $t_{p}$ ≤ 300 µs; δ ≤ 0.02; $T_{amb}$ = 25 °C; pulsed	-	85	270	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.8	-0.95	V
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.95	-1.1	V
		$I_{C}$ = -6 A; $I_{B}$ = -600 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-1.1	-1.25	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-0.7	-0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -3 A;	-	15	-	ns
r	rise time	$I_{Bon} = -150 \text{ mA}; I_{Boff} = 150 \text{ mA};$	-	220	-	ns
on	turn-on time	T <sub>amb</sub> = 25 °C	-	235	-	ns
S	storage time		-	160	-	ns
f	fall time		-	185	-	ns
off	turn-off time		-	345	-	ns

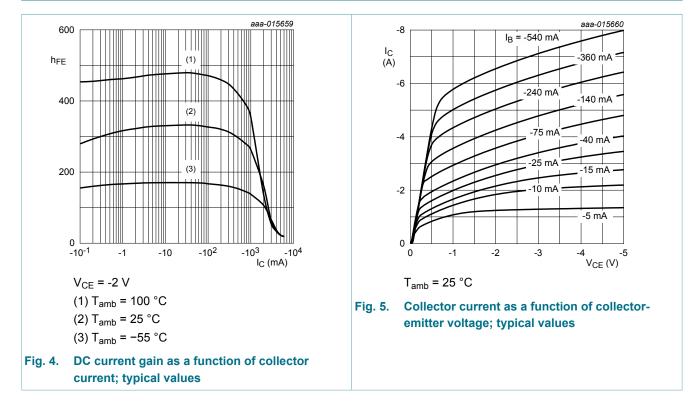
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -500 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	116	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	52	-	pF

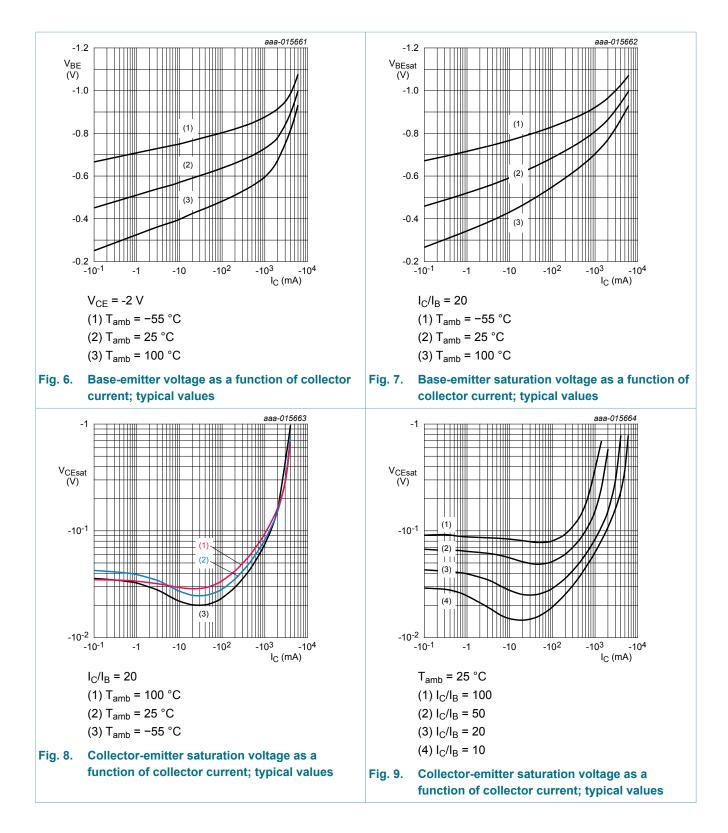


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#### 100 V, 6 A PNP high power bipolar transistor



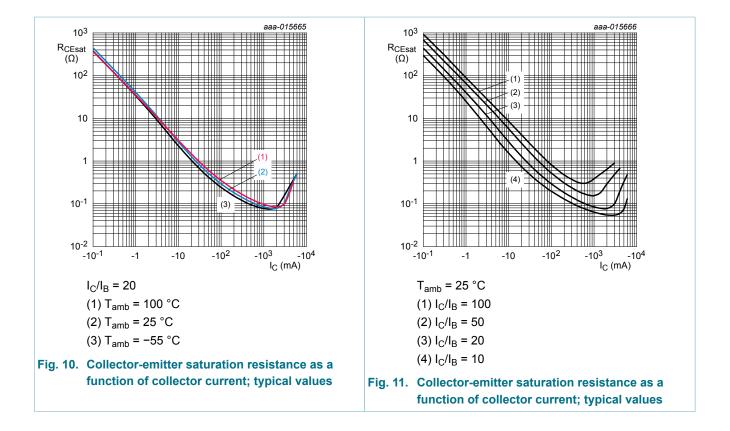
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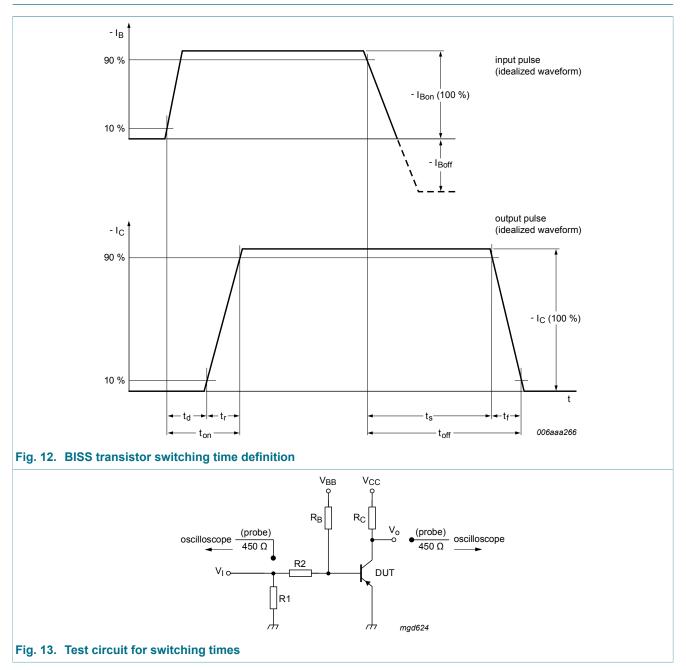
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#### 100 V, 6 A PNP high power bipolar transistor



### 11. Test information



This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

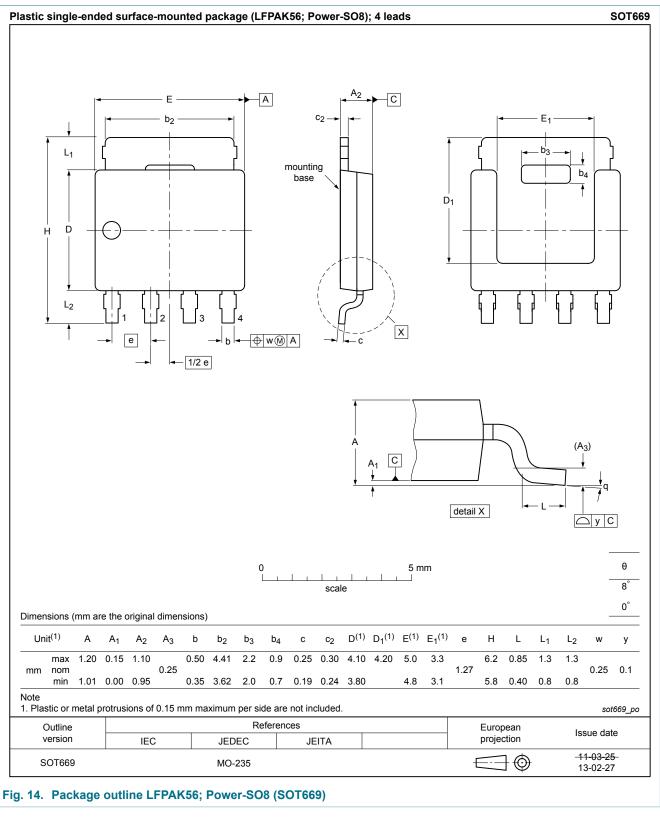
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### 12. Package outline



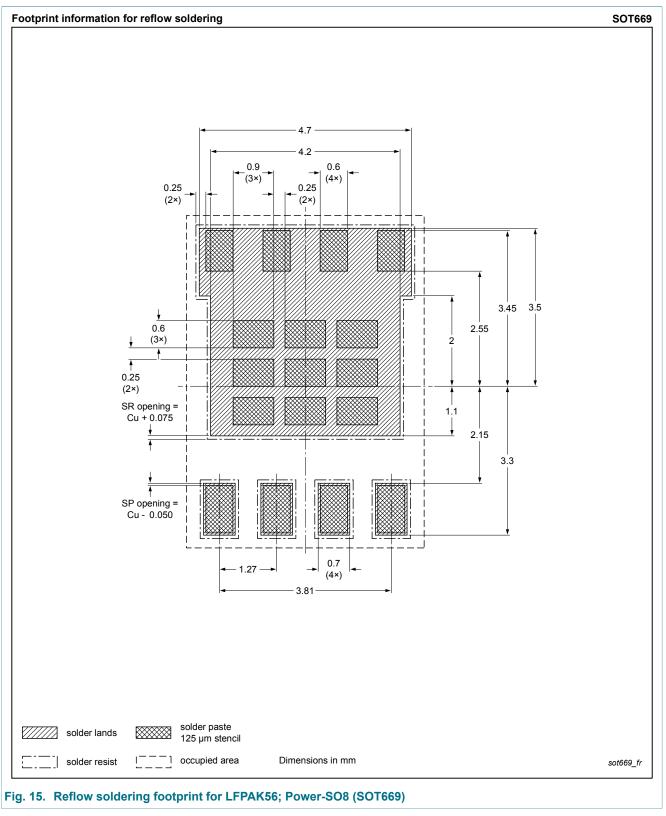
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### 13. Soldering



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#### 100 V, 6 A PNP high power bipolar transistor

# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT61006PY v.1	20150121	Product data sheet	-	-		

#### 100 V, 6 A PNP high power bipolar transistor

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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